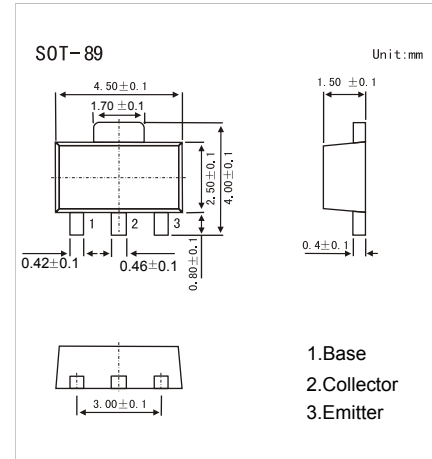


NPN Transistors

2SC4373

■ Features

- Collector Current Capability $I_c=800\text{mA}$
- Collector Emitter Voltage $V_{CE0}=120\text{V}$



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	120	V
Collector - Emitter Voltage	V_{CEO}	120	
Emitter - Base Voltage	V_{EBO}	5	
Collector Current - Continuous	I_c	800	mA
Collector Power Dissipation	P_c	500	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	250	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_c = 1\text{mA}, I_E = 0$	120			V
Collector- emitter breakdown voltage	V_{CEO}	$I_c = 10\text{mA}, I_B = 0$	120			
Emitter - base breakdown voltage	V_{EBO}	$I_E = 1\text{mA}, I_c = 0$	5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = 120\text{V}, I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5\text{V}, I_c = 0$			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = 500\text{mA}, I_B = 50\text{mA}$			1	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_c = 500\text{mA}, I_B = 50\text{mA}$			1.2	
Base - emitter voltage	V_{BE}	$V_{CE} = 5\text{V}, I_c = 500\text{mA}$			1	
DC current gain	h_{FE}	$V_{CE} = 5\text{V}, I_c = 100\text{mA}$	80		240	
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$			30	pF
Transition frequency	f_T	$V_{CE} = 5\text{V}, I_c = 0.5\text{A}$		120		MHz

■ Classification of h_{FE}

Type	2SC4373-O	2SC4373-Y
Range	80-160	120-240
Marking	CO	CY



炬芯微
XUANXINWEI

NPN Transistors

2SC4373

Typical Characteristics

